A2 B1 cont'l

6. (Amended) A method for forming a semiconductor device comprising:

irradiating a first laser light to a top surface of an object;

reflecting a second laser light at a reflector disposed on a back surface side of the object; and

irradiating the reflected second laser light to a back surface of the object,

wherein an effective energy intensity I_o of the first laser light to be applied onto the top surface is set at a level different from an effective energy intensity I_o' of the second laser light to be applied onto the back surface.

A3 Sub B2

9. (Amended) A method for forming a semiconductor device comprising:

irradiating a first laser light to a top surface of an object;

reflecting a second laser light at a reflector disposed on a back surface side of the object; and

irradiating the reflected second laser light to a back surface of the object,

wherein an effective energy intensity I_o of the first laser light to be applied onto the top surface and an effective energy intensity I_o' of the second laser light to be applied onto the back surface satisfy the relationship of $0 < I_o'/I_o < 1$ or $1 < I_o'/I_o$.

A4 Sub D1

21. (Amended) A method for forming a semiconductor device, comprising the steps of:

generating a laser light from a laser source used as an oscillating source;

dividing the laser light into a first laser light and a second laser light through an optical system;

attenuating the first laser light by an attenuation filter;

irradiating a top surface of an object with the attenuated first laser light; and

irradiating a back surface of the object with the second laser light.

24. (Amended) A method for forming a semiconductor device, comprising the steps of:

generating a laser light from a laser source used as an oscillating source;

dividing the laser light into a first laser light and a second laser light through an optical system;

attenuating the first laser light by an attenuation filter;

irradiating a top surface of an object with the attenuated first laser light; and

irradiating a back surface of the object with the second laser light,

wherein an effective energy intensity I_o of the first laser light to be applied onto the top surface is set at a level different from an effective energy intensity I_o' of the second laser light to be applied onto the back surface.

27. (Amended) A method for forming a semiconductor device, comprising the steps of:

generating a laser light from a laser source used as an oscillating source; and

dividing the laser light into a first laser light and a second laser light through an optical system;

attenuating the first laser light by an attenuation filter;

irradiating a top surface of an object with the attenuated first laser light; and

irradiating a back surface of the object with the second laser light,

wherein an effective energy intensity I_o of the first laser light to be applied onto the top surface and an effective energy intensity I_o' of the second laser light to be applied onto the back surface satisfy the relationship of $0 < I_o'/I_o < 1$ or $1 < I_o'/I_o$.

Please add new claims 30-33 as follows:

--30. A laser apparatus, comprising:

a laser source for emitting a laser light;

a half mirror for dividing the laser light into a first laser light and a second laser light;

an optical system for guiding the first laser light and the second laser light onto a top surface and a back surface of an object to be treated, respectively,

wherein the optical system includes a filter for attenuating the second laser light.

31. A method for forming a semiconductor device, comprising the steps of:

generating a laser light from a laser source used as an oscillating source;

dividing the laser light into a first laser light and a second laser light through an optical system;

attenuating the second laser light by an attenuation filter;

irradiating a top surface of an object with the first laser light; and

irradiating a back surface of the object with the attenuated second laser light.

32. A method for forming a semiconductor device, comprising the steps of:

generating a laser light from a laser source used as an oscillating source;

dividing the laser light into a first laser light and a second laser light through an optical system;

attenuating the second laser light by an attenuation filter;

irradiating a top surface of an object with the first laser light; and

irradiating a back surface of the object with the attenuated second laser light,

wherein an effective energy intensity I_o of the first laser light to be applied onto the top surface is set at a level different from an effective energy intensity I_o' of the second laser light to be applied onto the back surface.

33. A method for forming a semiconductor device, comprising the steps of:

generating a laser light from a laser source used as an oscillating source; and

dividing the laser light into a first laser light and a second laser light through an optical system;

A7

attenuating the second laser light by an attenuation filter;

irradiating a top surface of an object with the first laser light; and

irradiating a back surface of the object with the attenuated second laser light,

wherein an effective energy intensity I_o of the first laser light to be applied onto the top surface and an effective energy intensity I_o' of the second laser light to be applied onto the back surface satisfy the relationship of $0 < I_o'/I_o < 1$ or $1 < I_o'/I_o$.--

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the present application.

The Examiner's non-final Office Action dated November 28, 2001 has been received and its contents carefully noted. Claims 1-29 were pending in the present application. By this amendment, claims 4, 6, 9, 21, 24 and 27 have been amended and new claims 30-33 have been added. Accordingly, claims 1-33 are pending, of which claims 1, 4, 6, 9, 12, 15, 18, 21, 24, 27, and 30-33 are independent.

Claim 4 is not Anticipated By Baumgart or Xuan

Claim 4 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Baumgart et al., U.S. Patent No. 5,910,262 (Baumgart). Further, claim 4 stands rejected under 35 U.S.C. § 102(e) as being anticipated by Xuan, U.S. Patent No. 5,952,058 (Xuan).

The Applicants traverse the rejection by the Examiner, because both Baumgart and Xuan do not disclose all the elements of the claim, either explicitly or inherently.

The Examiner is reminded that in order to form a proper anticipation rejection under 35 U.S.C. § 102, the reference must disclose each and every element of the claimed invention. *See* M.P.E.P. § 2131; *Verdegaal Bros. v. Union Oil Co. of Cal.*, 814 F.2d 628, 631 (Fed. Cir. 1987); *Scripps Clinic & Res. Found. V. Genentech, Inc.*, 927 F.2d 1565, 1576 (Fed. Cir. 1991); *In re*